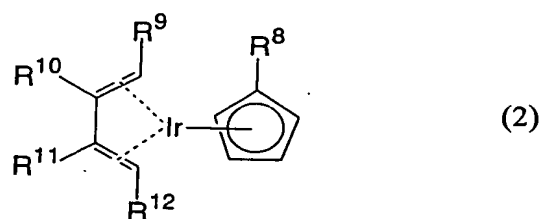
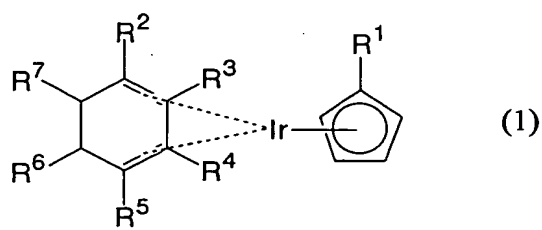


ABSTRACT OF THE DISCLOSURE

An organometallic compound having a low melting point, excellent vaporization characteristic and low film formation temperature on a substrate, for forming an iridium-containing thin film by the CVD process is provided. The organometallic iridium compound is represented by the following general formula (1) or (2):



wherein R¹ represents hydrogen or a lower alkyl group; R² to R⁷ each represents hydrogen, a halogen, or the like, provided that specific combinations of R¹ to R⁷ are excluded; R⁸ represents a lower alkyl group; R⁹ to R¹² each represents hydrogen, a halogen, or the like, provided that specific combinations of R⁸ to R¹² are excluded. Iridium-containing thin films are produced by using the compound as a precursor by CVD process.